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# Direct RF to Optical Link Based on Film Bulk Acoustic Wave Resonators (FBAR)

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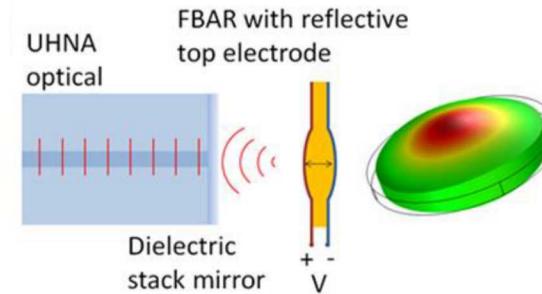
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# FBAR based Optical Modulator

- Introduction
- Overview of FBAR concept
- Theoretical Analysis of System Performance
  - Optical Characteristics
  - RF/mechanical Characteristics
- Experimental Demonstration
  - Electrical Characterization
  - Optic Characterization
  - System Performance
- Conclude

# Introduction

- Variety of approaches to phase modulation
  - Silicon photonics phase modulator approaches based on carrier injection
  - Nonlinear Optics
  - Opto-mechanics
  - MEMS based approaches
  - Plasmonics
- FBAR approach → Small displacement will be resonantly enhanced optically and mechanically
  - Low  $V_\pi$
  - High power handling
  - Relatively compact

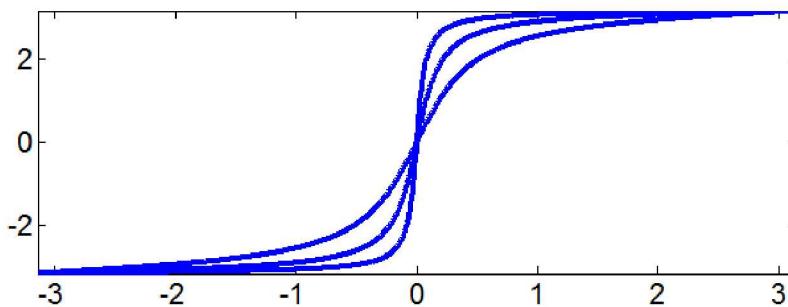


# FBAR modular Phase Response

- System response is determined by the optical phase response and the FBAR response

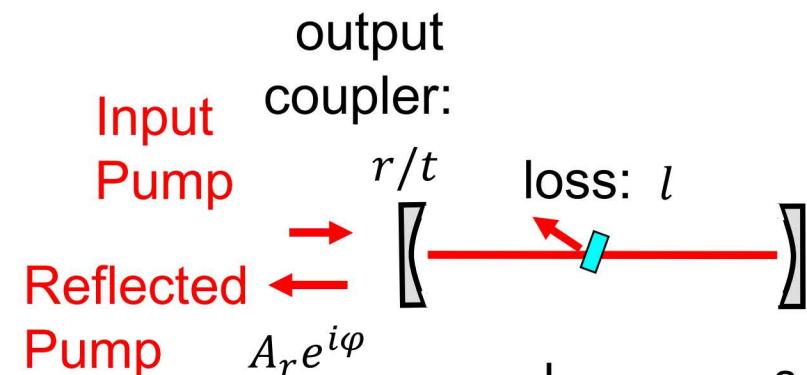
$$\frac{d\theta}{dV} = \frac{d\varphi}{ds} \times \frac{2\pi}{\lambda} \frac{ds}{dV}$$

- Optical phase response

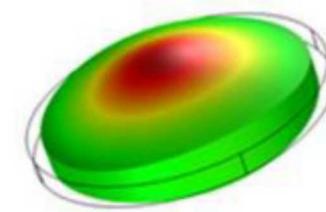


$$r_{refl} = r - \left( \frac{t^2(1-l)^{.5} \exp(i\varphi)}{1 - r(1-l)^{.5} \exp(i\varphi)} \right)$$

$\frac{d\varphi}{ds}$  Is determined by optical finesse

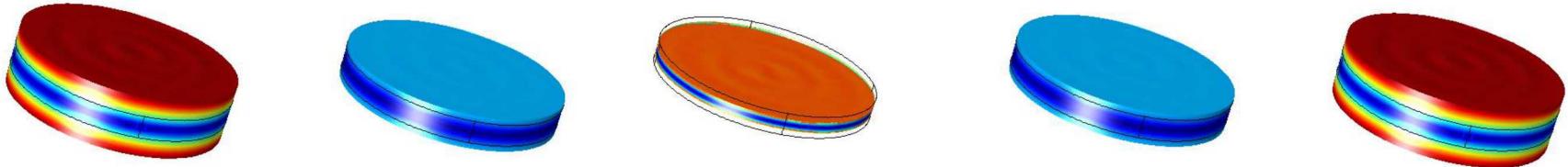


- Mechanical Displacement
  - Dilatational mode
    - Frequency set by film thickness
    - Displacement set by  $K_t^2$  and mechanical Q

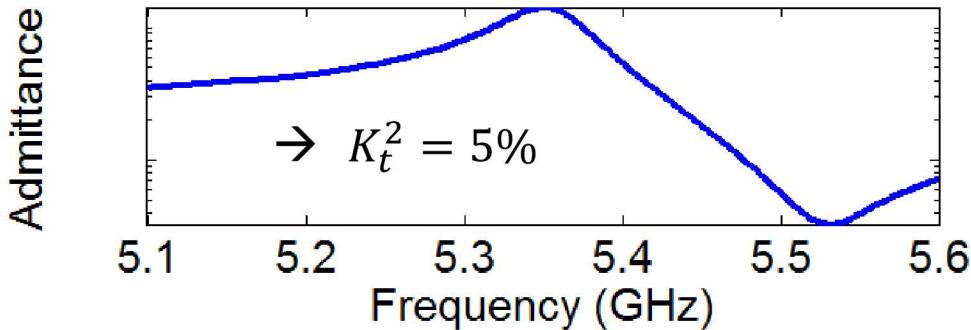


- Optimal response with large optical finesse and mechanical Q

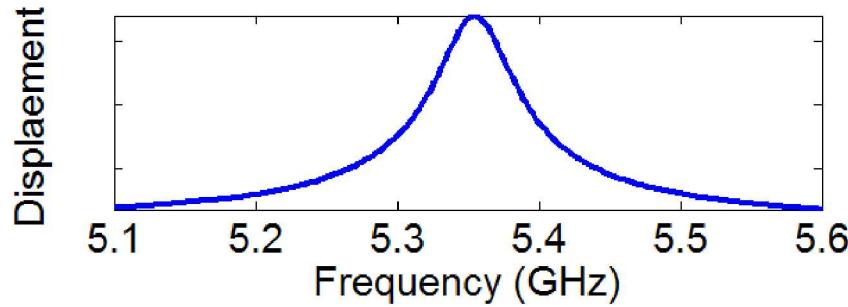
# FEM Simulation of FBAR Response



- Resonant frequency for dilatational mode is set by film thickness



- The product  $K_t^2 \times Q$  determines  $\frac{ds}{dV}$



## Electro-mechanical coupling

$K_t^2 \rightarrow$  determined by series and parallel resonances

## Quality factor

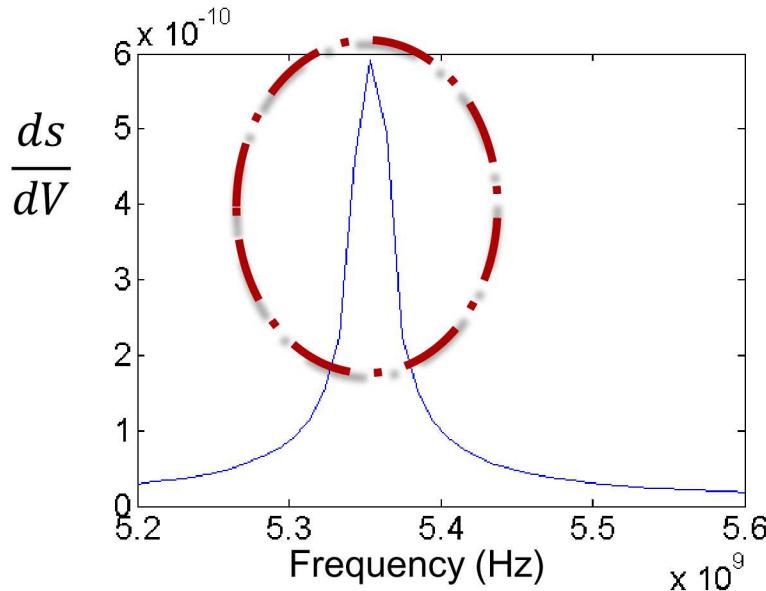
$Q \rightarrow$  Needs to be low to have reasonable bandwidth

$$\rightarrow \frac{ds}{dV} = .5 \text{ nm/Volt}$$

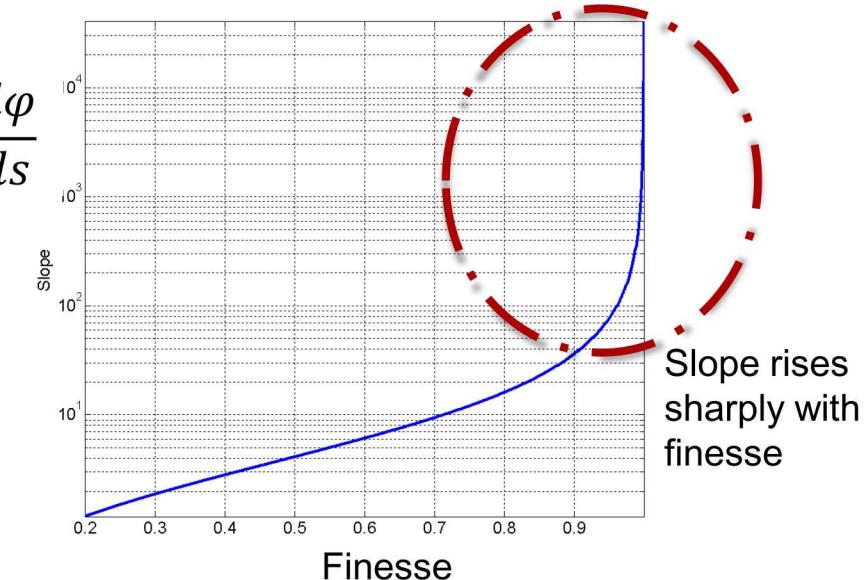
Want large  $K_t^2$

# Required Optical Finesse From Model

## FBAR mechanical response



## Cavity Optical response



- Without Optical or mechanical Resonances  $V_\pi$  is large (1kV)

$$\frac{d\theta}{dV} = \frac{d\varphi}{ds} \times \frac{2\pi}{\lambda} \frac{ds}{dV}$$

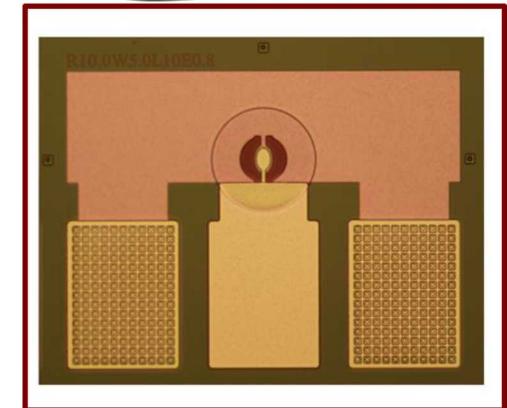
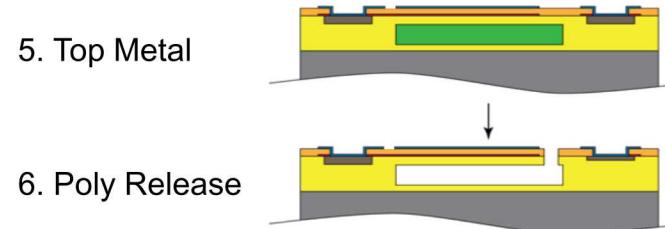
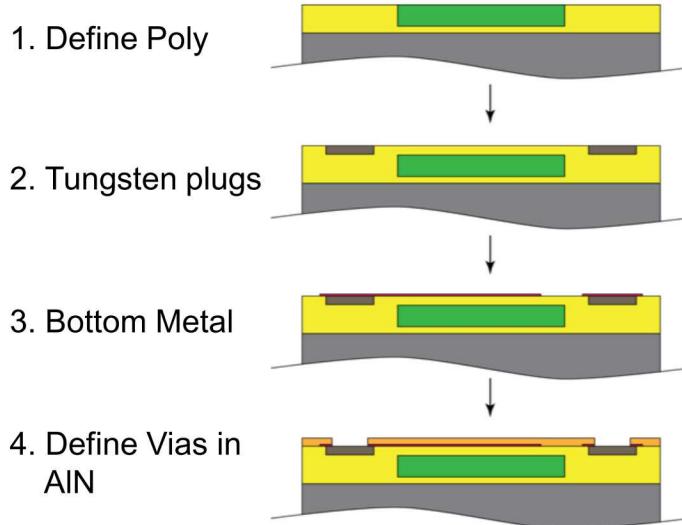
.5nm/Volt  
 $2\pi/1550\text{nm}$

- In order to achieve a  $V_{pi}$  on the order for 1Volt

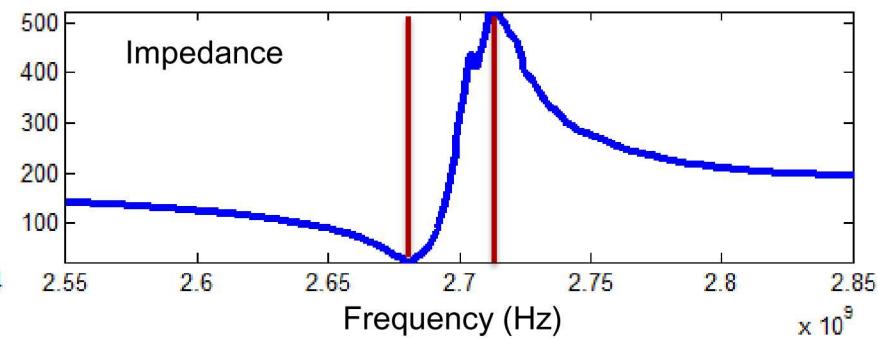
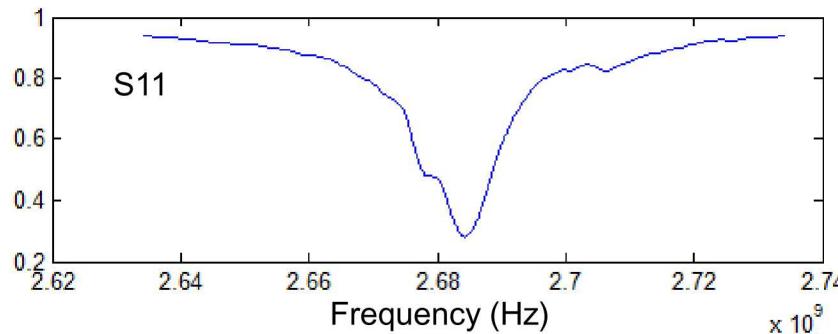
$\frac{ds}{dV}$  → Need high mechanical Q  $\sim 100$   
 $\frac{d\varphi}{ds}$  → Slope on the order of 1000

$\frac{d\varphi}{ds}$  → Want high optical Finesse  
 $\frac{ds}{dV}$  → Slope on the order of 1000

# Fabrication and Electrical Characterization



- Electrical Testing Confirms Film Quality

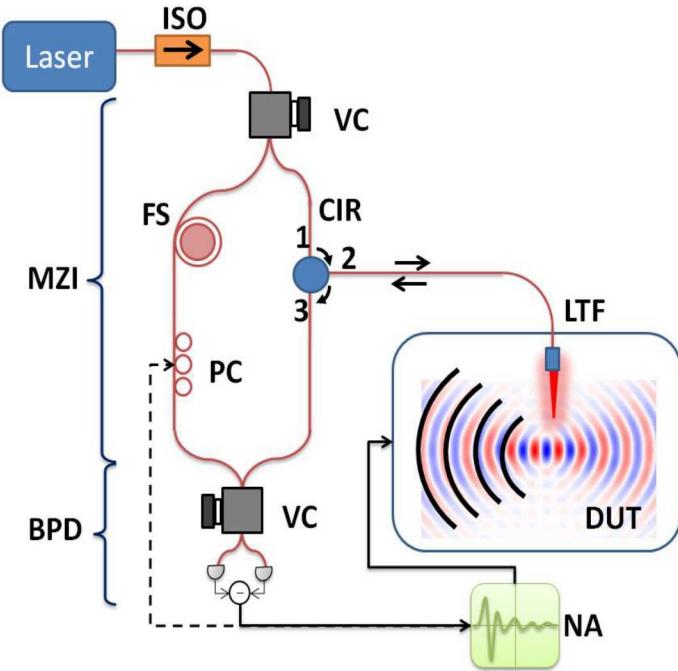


$Q = 63 \rightarrow$  Targeting a bandwidth of a few percent around center frequency

$K_t^2 = 3.5\% \rightarrow$  determined by series and parallel resonances

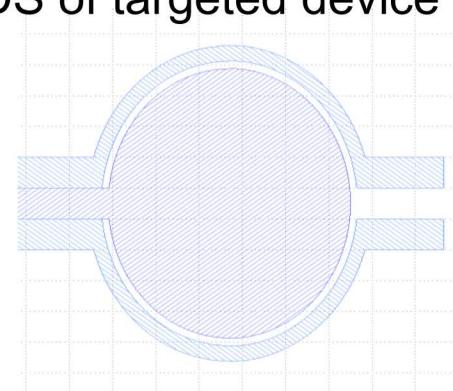
# Optical Experimental Characterization

- Scanning confocal balanced homodyne interferometer for Doppler vibrometry

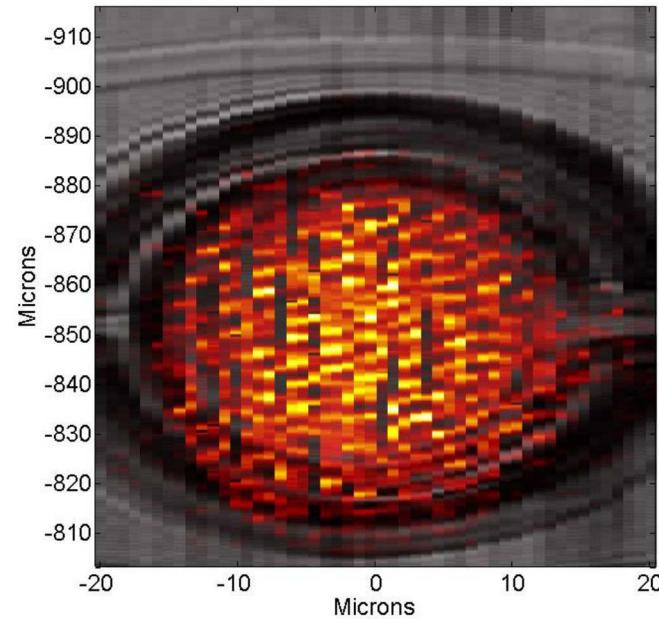


Displacement field overlaid with confocal image

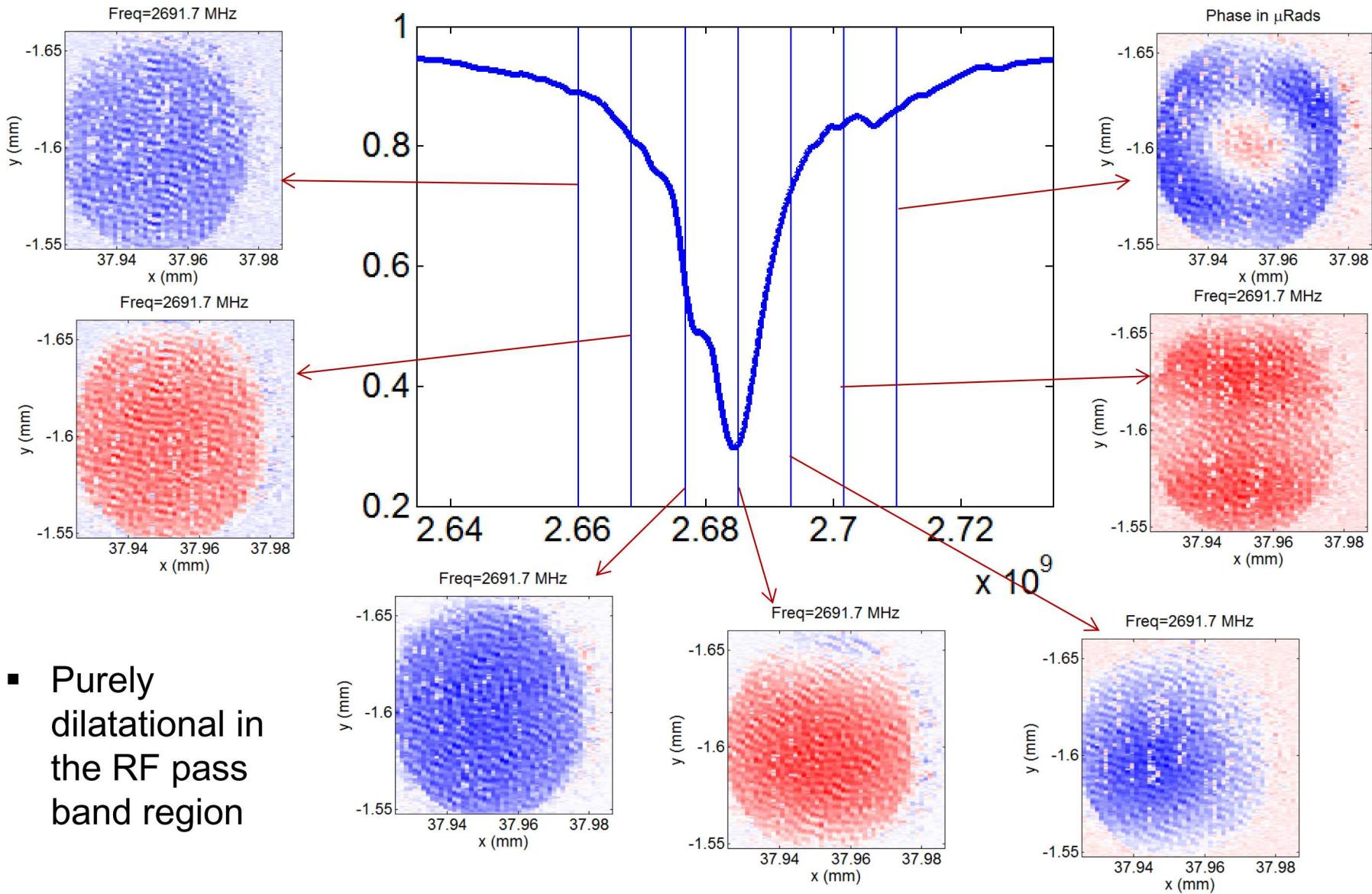
- GDS of targeted device



- Displacement field amplitude



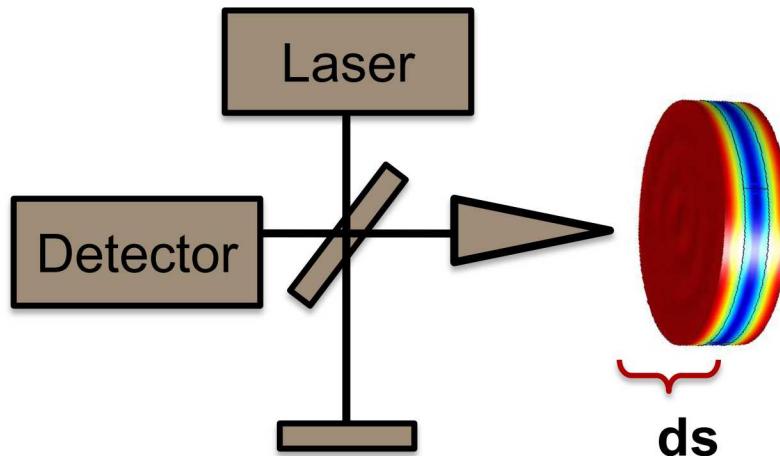
# Mode Profile Across Resonance



- Purely dilatational in the RF pass band region

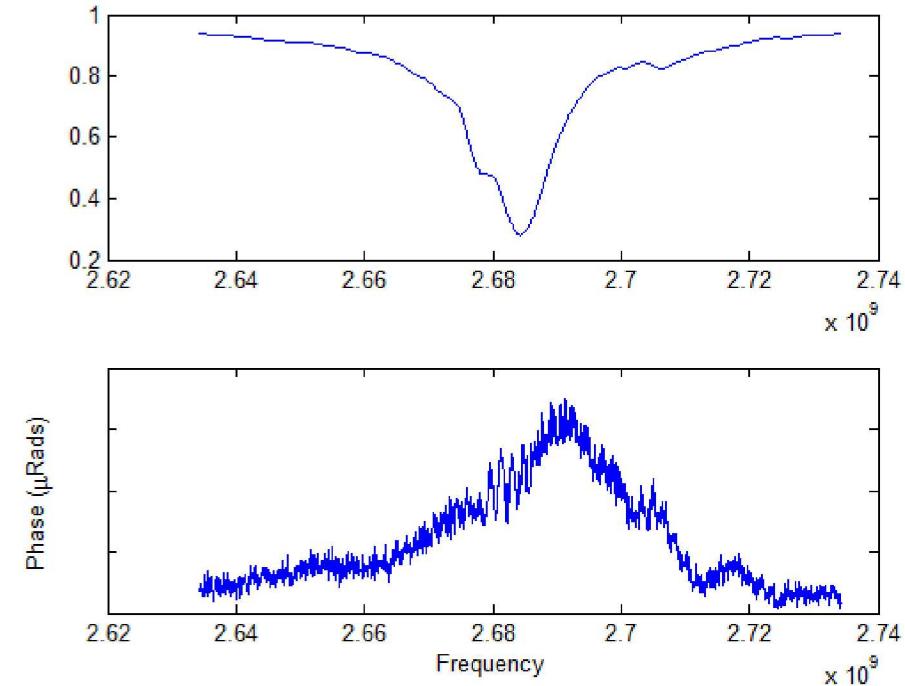
# Calibrated Phase Measurement

- Lens Taper Fiber (LTF) is positioned at center of large area FBAR



- FBAR driven with fixed RF power causing displacement amplitude, **ds**
- Detector measures  $d\theta$  for a given voltage:

$$d\theta = \frac{d\varphi}{ds} \times \frac{2\pi}{\lambda} \times \frac{ds}{dV} \times \Delta V$$



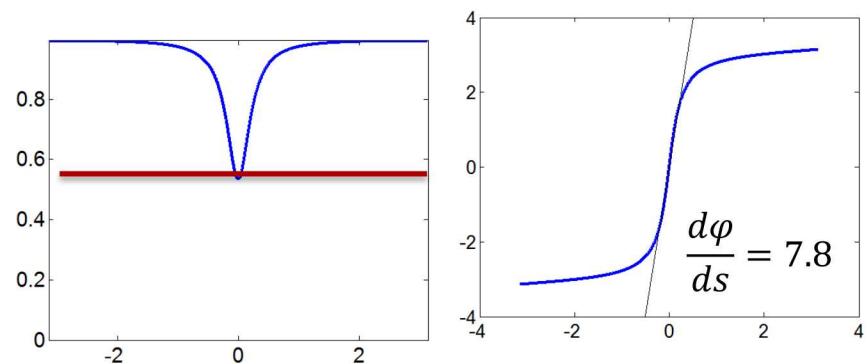
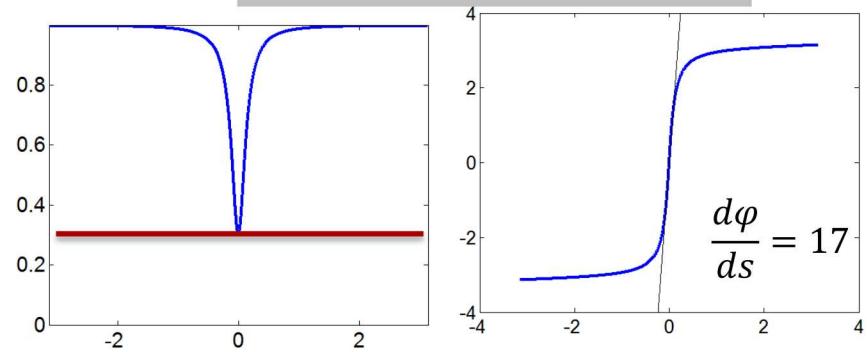
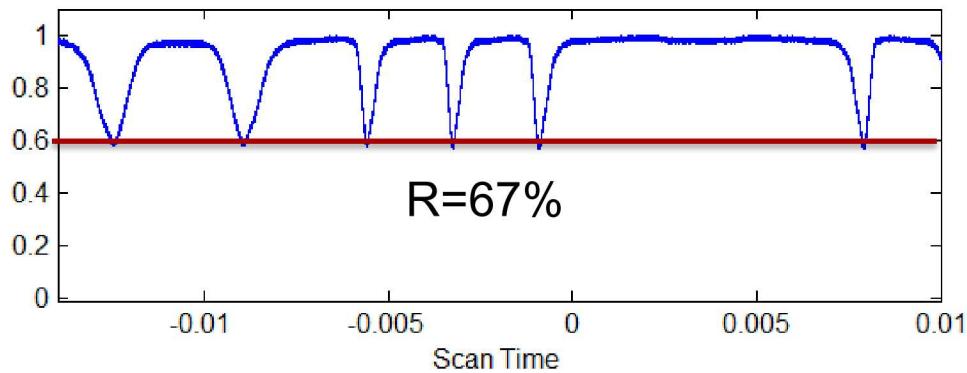
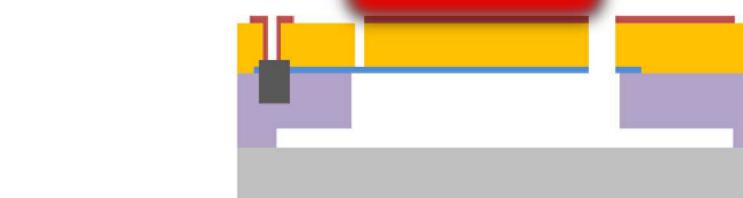
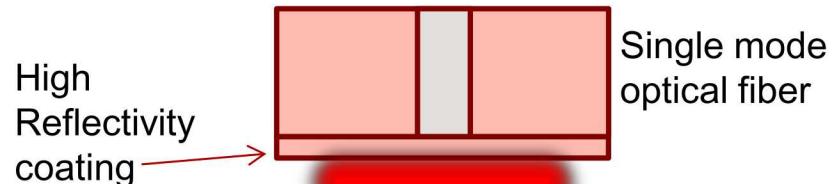
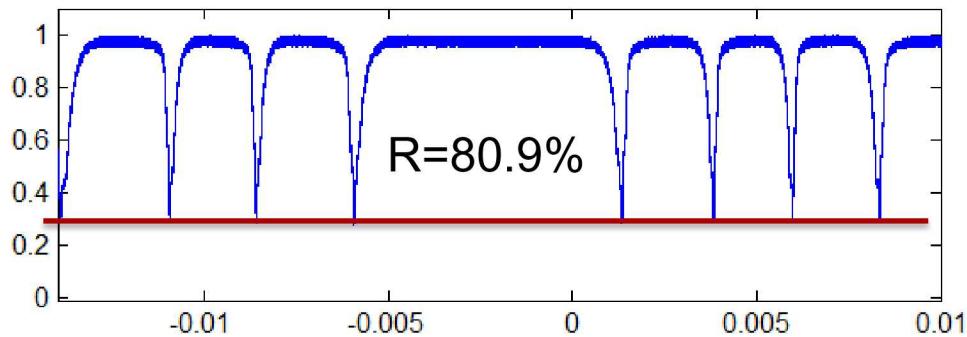
- From these results we can determine  $V_\pi$

$$V_\pi = .4V / 300 \mu\text{Rad} \times \pi = 1.3\text{kV}$$

→ Optical cavity need to reduce  $V_\pi$

# Dielectric Coated Fiber

- Reflected power with coated fibers with different reflectivities



- Reflected power consistent with 7-8% loss

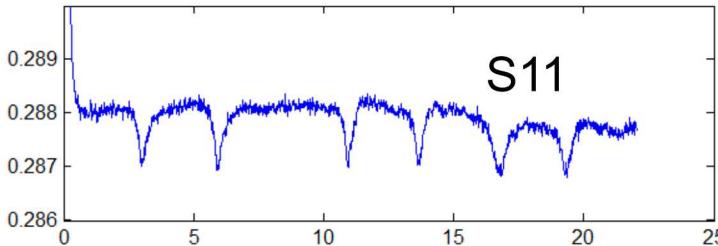
$$r_{refl} = r - \left( \frac{t^2(1-l)^5 \exp(i\varphi)}{1 - r(1-l)^5 \exp(i\varphi)} \right)$$

# Phase Response Enhancement from Optical Finesse

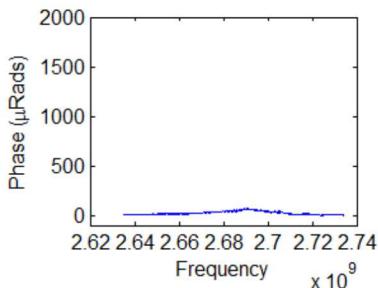
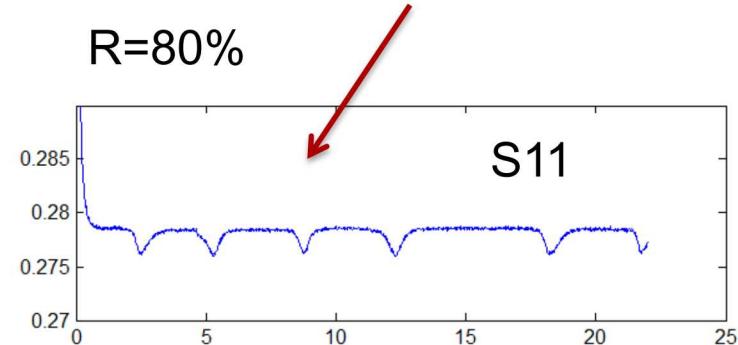
Presence of cavity mode shifts Impedance

LTF

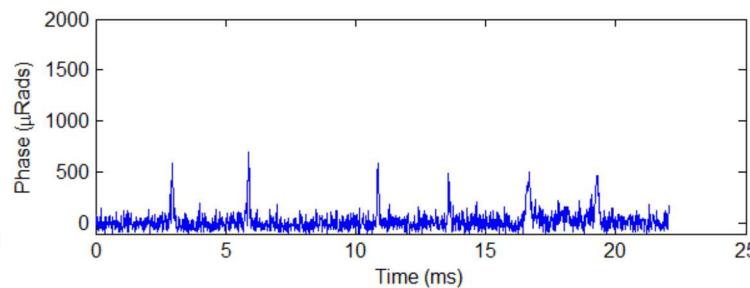
R=67%



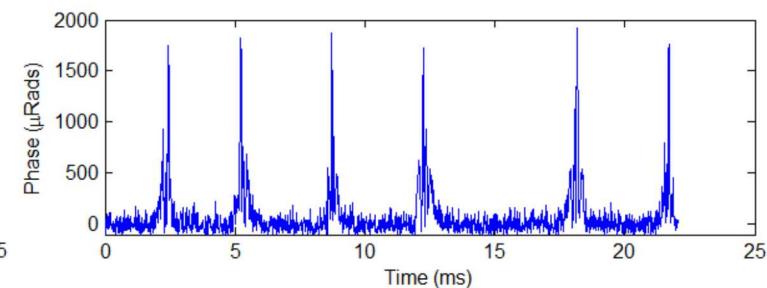
R=80%



×1



×6

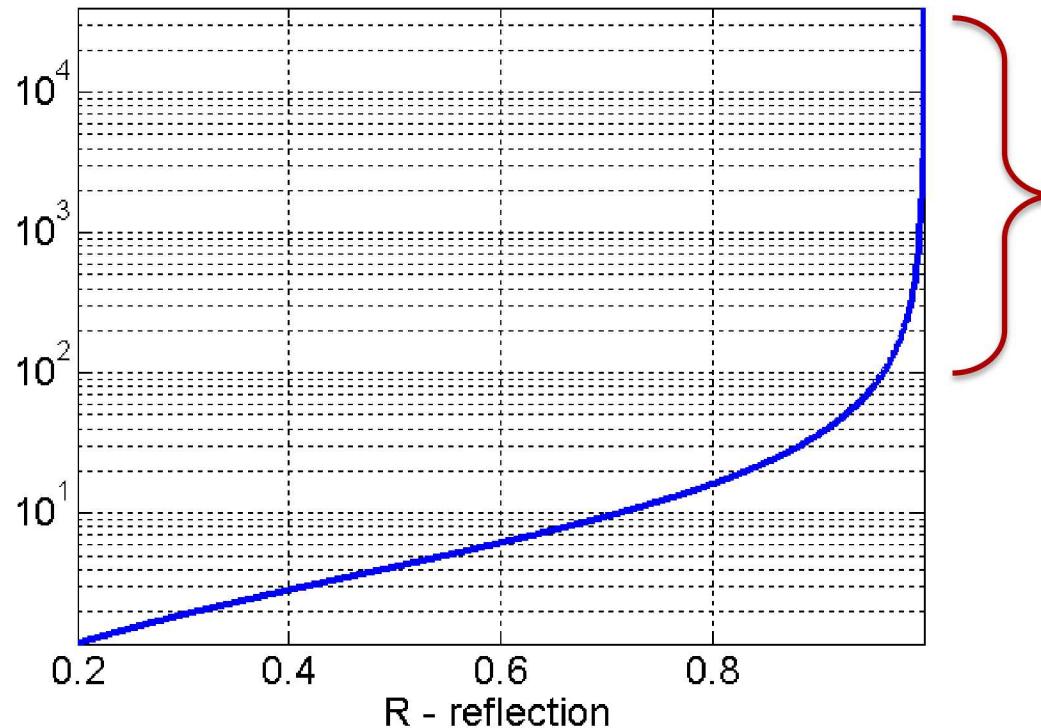


×18 larger than without cavity

- Phase response increases by the optical finesse
- Reduction in  $V_{pi}$  by optical enhancement
- Driven with 5dBm RF power

# Phase Response Enhancement from Optical Finesse

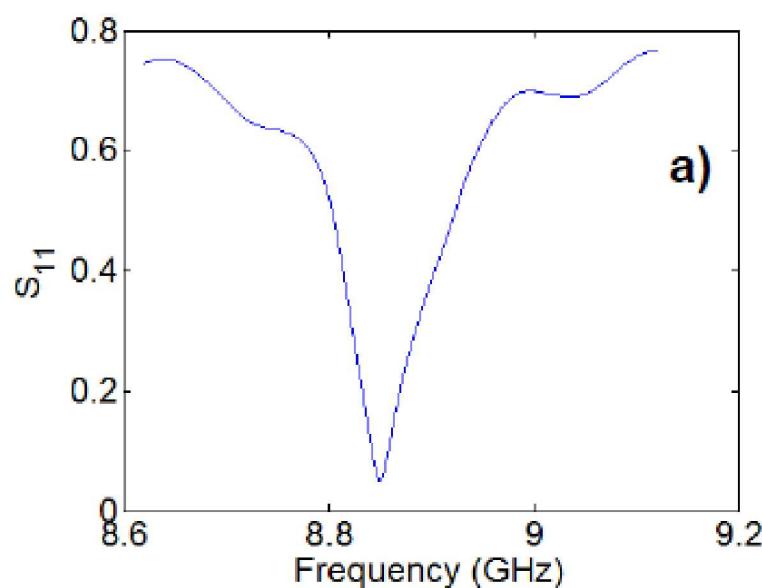
- Reduce intracavity optical loss to the .6% range



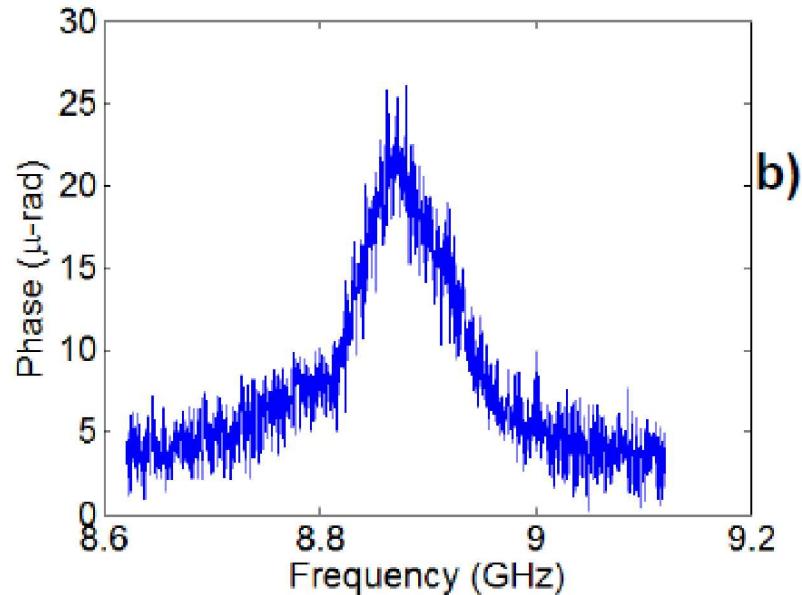
High finesse will bring  $V_{pi}$  down to the few volts range

- Large improvement as finesse increases
- Improvement in mechanical Q factor
- Should get  $V_{pi}$  down to a few volts

# High Speed Devices



a)

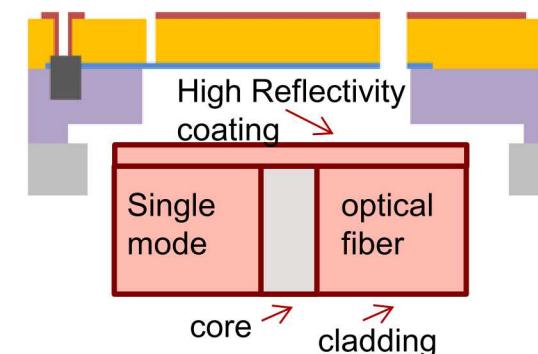


b)

- Thinner membrane device increases resonance frequency
- of 20  $\mu$ -rad with 0dBm RF-excitation at 8.85GHz
- Finesse on the order of 1000 we expect a  $V_{pi}$  in the few volt range

# Conclusion

- Proposed a way to use FBARS and a coated and cleaved fiber end to achieve high speed modulators in a Fabry-Perot configuration
- Numerically modeled system performance
- Shown that  $V_{pi}$  in the few volt range is possible given experimental parameters
- This concept has high power handling and monolithic integration, however it is narrow band.
- Improve fiber deposition quality and top metal reflectivity



# Thank you